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(54) Title: SOLUTION BASED PRECURSORS

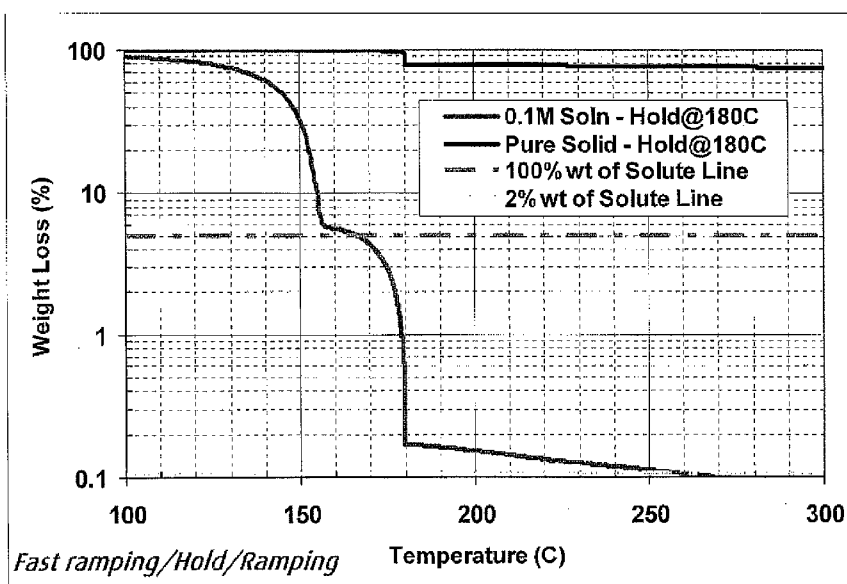


FIG. 2

(57) Abstract: Solution-based precursors for use as starting materials in film deposition processes, such as atomic layer deposition, chemical vapor deposition and metalorganic chemical vapor deposition. The solution-based precursors allow for the use of otherwise solid precursors that would be unsuitable for vapor phase deposition processes because of their tendency to decompose and solidify during vaporization.